

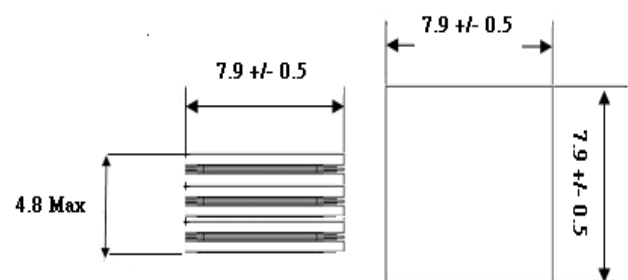
MDE Semiconductor, Inc.

SMD30KPA CELL DATA SHEET (SILICON-AVALANCHE HIGH SURGE DIODES)

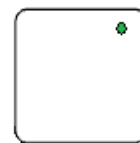
Preliminary

FEATURES

- . Glass passivated chip junction
- . Bipolar electrical characteristics
- . 30000W peak pulse power capability on 10/1000us waveform
- . Excellent clamping capability
- . Repetition rate (duty cycle) : 0.05%
- . Low incremental surge resistance
- . Fast response time: typically less than 1.0ps
from 0 Volts to BV



Dimensions in Millimeters



Dot mark for A Series

MECHANICAL DATA

Terminal: Silver plated lead ,solderable per MIL-STD-750,Method 2026

Mounting Position : Any for CA Series

Weight: 2.2±0.1g

SMD30KPA PART NUMBER		REVERSE STAND-OFF VOLTAGE $V_{RWM}(V)$	BREAKDOWN VOLTAGE $V_{BR}(V)$ MIN. @ I_T	TEST CURRENT I_T (mA)	PEAK PULSE CURRENT I_{pp} (A)	REVERSE LEAKAGE @ V_{RWM} $I_R(\mu A)$	MAXIMUM CLAMPING VOLTAGE @ I_{pp} V_C (V)
UNI-POLAR	BI-POLAR						
SMD30KPA17A	SMD30KPA17CA	17	18.99	50	1023.9	5000	29.3
SMD30KPA60A	SMD30KPA60CA	60	67.0	5	297.1	5	102.0
SMD30KPA280A		280	312.8	5	65.3	2	464.0

For bidirectional type having V_{rwm} of 30 volts and less, the I_R limit is double.